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Shoji Tanaka
Yutaka Toyozawa

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PREFACE

The Fifteenth International Conference on the Physics of Semiconductors was held at the Kyoto International Conference Hall from September 1 through 5, 1980. The Hall is located in the suburbs of Kyoto, the old capital of Japan, surrounded by small hills. There were over 800 participants from 32 countries.

The Conference was sponsored by the International Union of Pure and Applied Physics, and organized by the Science Council of Japan and the Physical Society of Japan. We wish to thank these organizations as well as all other private organizations and companies which gave us the substantial support.

The Conference Program was arranged in 48 technical sessions which were grouped into four simultaneous sessions, except the opening, plenary and closing sessions. A special session was devoted to the interfacial problems between applied and basic studies of semiconductors. As a whole there were 4 plenary, 26 invited and 244 contributed papers. The Program was made by the International Program Committee, which was held at Tokyo on May 6 and 7. It was quite a difficult task to select the papers from over 600 abstracts. We would like to thank the Program Committee, especially its overseas members who came all these miles to Tokyo, for performing this essential task for the Conference in a tight schedule. We regret that many good papers could not be accommodated in the Program because of the limitation in time and space. A book of abstracts was distributed to participants at the Conference.

The papers in the Proceedings follow in principle the Program of the Conference, but a small rearrangement was made as we had not any restriction in time and space which had bound the Program. Some of the sessions in the Program were combined into one session, and the papers were put into a slightly different order and in a few cases, new titles were introduced. These changes were made in order to facilitate the readers to get insights into the latest progress in the field of semiconductor physics. All papers were reviewed by 14 referees.

The members of the Conference Committees are listed on the following page. We are very grateful to them as well as to all the authors of papers for their work and cooperation. We would also like to thank other people whose names were not listed but who have worked quite hard for editing the Proceedings. Finally, we express our gratitude to the Yamada Science Foundation which supported partly for the publication of the Proceedings.

November, 1980

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